



High Voltage NPN Transistor with Diode



TO-251 (IPAK)



TO-252

Pin Definition:

- 1. Base
- 2. Collector
- 3. Emitter

PRODUCT SUMMARY

Block Diagram

=0.1A

Features

- Build-in Free-wheeling Diode Makes Efficient Antisaturation Operation
- Low Base Drive Requirement
- Suitable for Half Bridge Light Ballast Application

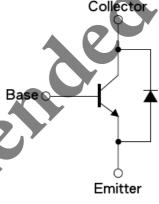
Structure

- Silicon Triple Diffused Type
- **NPN Silicon Transistor**
- Integrated Anti-parallel Collector-Emitter Diode

Ordering Information

Part No.	Package	Packing
TSC5304EDCP ROG	TO-252	2.5Kpcs / 13" Reel
TSC5304EDCH C5G	TO-251	75pcs / Tube

Note: "G" denote for Halogen Free Product



Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	700	V
Collector-Emitter Voltage @ V _{BE} =0V	V _{CES}	700	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	Ic	4	А
Collector Peak Current (tp <5ms)	I _{CM}	8	Α
Base Current	I _B	2	Α
Base Peak Current (tp <5ms)	I _{BM}	4	Α
Power Total Dissipation @ Tc=25°C	P _{DTOT}	35	W
Maximum Operating Junction Temperature	TJ	+150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

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Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	3.57	°C/W
Thermal Resistance - Junction to Ambient	R⊖ _{JA}	68	°C/W

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_C = 1 \text{mA}, I_B = 0$	BV_CBO	700		Ð	V
Collector-Emitter Breakdown Voltage	$I_{C} = 10 \text{mA}, I_{E} = 0$	BV_CEO	400		1	V
Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	BV_{EBO}	9	4	1	V
Collector Cutoff Current	$V_{CB} = 700 \text{V}, I_E = 0$	I _{CBO}			100	uA
Collector Cutoff Current	$V_{CE} = 400V, I_{B} = 0$	I _{CEO}			250	uA
Emitter Cutoff Current	$V_{EB} = 7V$, $I_C = 0$	I _{EBO}			10	uA
	$I_C = 0.5A, I_B = 0.1A$	V _{CE(SAT)1}		0.25	0.7	
Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$	V _{CE(SAT)2}		0.5	1	V
	$I_C = 2.5A, I_B = 0.5A$	V _{CE(SAT)3}		1.2	1.5	
	I _C =4A, I _B =1A	$V_{CE(SAT)4}$		0.5		
Book Emitter Caturation Voltage	$I_{C} = 1A, I_{B} = 0.2A$	V _{BE(SAT)1}		1.1	V	
Base-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 0.5A$	$V_{BE(SAT)2}$			1.2	V
	$V_{CE} = 5V$, $I_{C} = 10mA$		10			
DC Current Gain	$V_{CE} = 5V$, $I_{C} = 1A$	Hfe	17		37	
	$V_{CE} = 5V$, $I_{C} = 2A$		12		32	
Forward Voltage Drop	I _F =2A	Vf			2	V
Turn On Time	V_{CC} =250V, I_{C} =1A,	t _{ON}		0.2	0.6	uS
Storage Time	$I_{B1} = I_{B2} = 0.2A$, $t_p = 25uS$	t _{STG}		3.0	4.5	uS
Fall Time	Duty Cycle<1%	t _f		0.2	0.3	uS
Turn On Time	$V_{CC} = 5V, I_{C} = 0.1A,$	t _{ON}		0.35	0.6	uS
Storage Time	$I_{B1}=I_{B2}=0.02A$, $t_p=25uS$	t _{STG}	6.5		8.5	uS
Fall Time	Duty Cycle<1%	t _f		0.3	0.6	uS

Notes: Pulsed duration =380uS, duty cycle ≤2%

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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics 6.0 lb=900mA lb=800mA lb=700mA Ic[A], Collector Current 5.0 lb=600mA lb=500mA lb=400mA 4.0 lb=300mA 3.0 lb=200mA . Ib=100mA 2.0 1.0 Ib=10mA 0 0 6 8 10 Vce[V], Collector-Emitter Voltage

Figure 2. DC Current Gain 30 Vce=10V He DC Current Gain 20 10 0.01 10 c[A], Collector Current

Figure 3. Vce(sat) v.s. Vbe(sat)

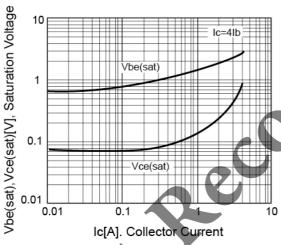


Figure 4. Power Derating

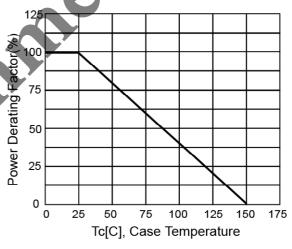


Figure 5. Reverse Bias SOA

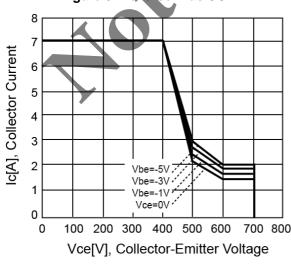
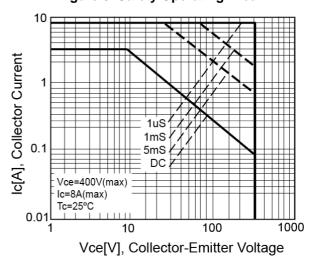


Figure 6. Safety Operating Area



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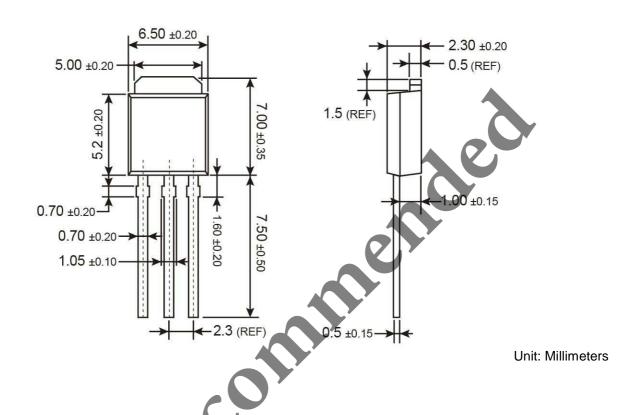
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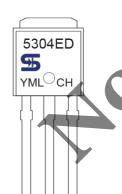




TO-251 Mechanical Drawing



Marking Diagram



Y = Year Code

= Month Code for Halogen Free Product

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(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep,

X=Oct, Y=Nov, Z=Dec)

= Lot Code

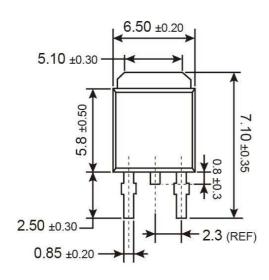
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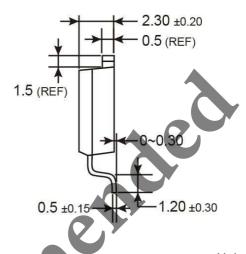




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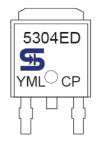
TO-252 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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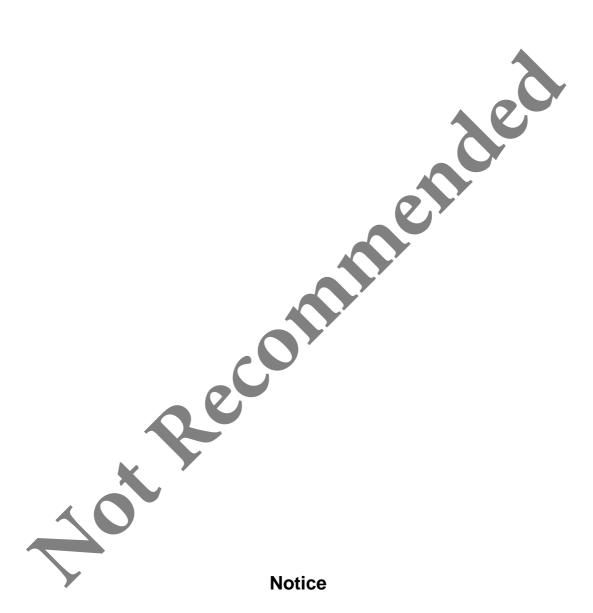
L = Lot Code

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Pb RoHS

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